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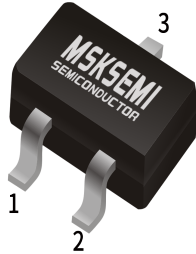


GDT



PLED

Product data sheet

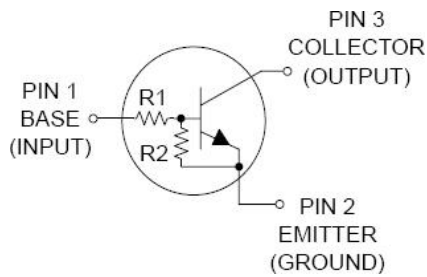


SOT-523

Features:

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	50	V
V_{CE0}	Collector-Emitter Voltage	50	V
I_c	Collector Current	100	mA
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	600	$^\circ\text{C} / \text{W}$
$T_J T_{STG}$	Junction & Storage Temperature Range	-55 to +150	$^\circ\text{C}$

These ratings are limiting values above which the serviceability of the device may be impaired.

Device Marking & Resistor Values:

P/N	Mark	R1 (KΩ)	R2 (KΩ)
DTC114EE-MS	24	10	10
DTC124EE-MS	25	22	22
DTC144EE-MS	26	47	47
DTC114YE-MS	64	10	47
DTC114TE-MS	04	10	∞
DTC143TE-MS	03	4.7	∞
DTC123EE-MS	22	2.2	2.2
DTC143EE-MS	23	4.7	4.7
DTC143ZE-MS	E23	4.7	47
DTC124XE-MS	45	22	47
DTC123JE-MS	E42	2.2	47

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Typ	Max	
I_{CBO}	Collector-Base Cutoff Current	$V_{CB} = 50\text{V}, I_E = 0\text{A}$	-	-	100	nA
I_{CEO}	Collector-Emitter Cutoff Current	$V_{CE} = 50\text{V}, I_B = 0\text{A}$	-	-	500	nA
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB} = 6.0\text{V}, I_C = 0\text{A}$				
	DTC114EE-MS		-	-	0.50	mA
	DTC124EE-MS		-	-	0.20	
	DTC144EE-MS		-	-	0.10	
	DTC114YE-MS		-	-	0.20	
	DTC114TE-MS		-	-	0.90	
	DTC143TE-MS		-	-	1.90	
	DTC123EE-MS		-	-	2.30	
	DTC143EE-MS		-	-	1.50	
	DTC143ZE-MS		-	-	0.18	
	DTC124XE-MS		-	-	0.13	
	DTC123JE-MS		-	-	0.20	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0\text{A}$	50	-	-	Volts
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Note 1)	$I_C = 2.0\text{mA}, I_B = 0\text{A}$	50	-	-	Volts

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%

On Characteristics (Note 1)

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Typ	Max	
H_{FE}	DC Current Gain	$V_{CE} = 10V, I_C = 5.0mA$				
	DTC114EE-MS		35	60	--	
	DTC124EE-MS		60	100	--	
	DTC144EE-MS		80	140	--	
	DTC114YE-MS		80	140	--	
	DTC114TE-MS		160	350	--	
	DTC143TE-MS		160	350	--	
	DTC123EE-MS		8.0	15	--	
	DTC143EE-MS		15	30	--	
	DTC143ZE-MS		80	200	--	
	DTC124XE-MS		80	150	--	
	DTC123JE-MS		80	140	--	
V_{CE(sat)}	Collector-Emitter Saturation Voltage					
	DTC114EE-MS	$I_C = 10mA, I_B = 0.3mA$				
	DTC124EE-MS	$I_C = 10mA, I_B = 0.3mA$				
	DTC144EE-MS	$I_C = 10mA, I_B = 0.3mA$				
	DTC114YE-MS	$I_C = 10mA, I_B = 0.3mA$				
	DTC114TE-MS	$I_C = 10mA, I_B = 1mA$	--	--	0.25	Volts
	DTC143TE-MS	$I_C = 10mA, I_B = 1mA$				
	DTC123EE-MS	$I_C = 10mA, I_B = 5mA$				
	DTC143EE-MS	$I_C = 10mA, I_B = 1mA$				
	DTC143ZE-MS	$I_C = 10mA, I_B = 1mA$				
	DTC124XE-MS	$I_C = 10mA, I_B = 1mA$				
	DTC123JE-MS	$I_C = 10mA, I_B = 0.3mA$				
V_{OL}	Output Voltage (on)	$R_L = 1.0K\Omega$				
	DTC114EE-MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC124EE-MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC144EE-MS	$V_{CC} = 5.0V, V_B = 3.5V$				
	DTC114YE-MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC114TE-MS	$V_{CC} = 5.0V, V_B = 2.5V$	--	--	0.20	Volts
	DTC143TE-MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC123EE--MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC143EE--MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC143ZE--MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC124XE--MS	$V_{CC} = 5.0V, V_B = 2.5V$				
	DTC123JE--MS	$V_{CC} = 5.0V, V_B = 2.5V$				

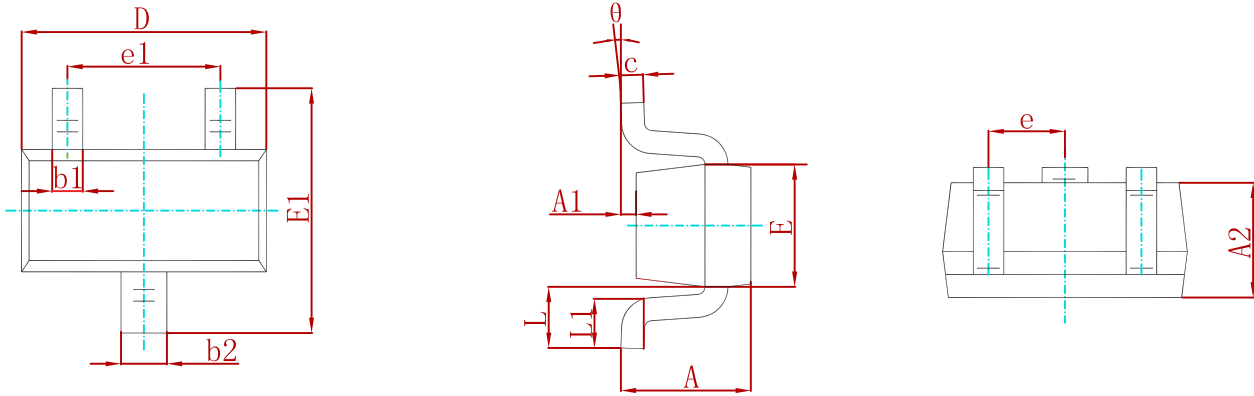
On Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Typ	Max	
V _{OH}	Output Voltage (on)	R _L = 1.0KΩ	4.9	--	--	Volts
		DTC114EE V _{CC} =5.0V, V _B =0.5V				
		DTC124EE V _{CC} =5.0V, V _B =0.5V				
		DTC144EE V _{CC} =5.0V, V _B =0.5V				
		DTC114YE V _{CC} =5.0V, V _B =0.5V				
		DTC114TE V _{CC} =5.0V, V _B =0.25V				
		DTC143TE V _{CC} =5.0V, V _B =0.25V				
		DTC123EE V _{CC} =5.0V, V _B =0.5V				
		DTC143EE V _{CC} =5.0V, V _B =0.5V				
		DTC143ZE V _{CC} =5.0V, V _B =0.25V				
		DTC124XE V _{CC} =5.0V, V _B =0.5V				
		DTC123JE V _{CC} =5.0V, V _B =0.5V				

Electrical Characteristics (T_A = 25°C unless otherwise noted)

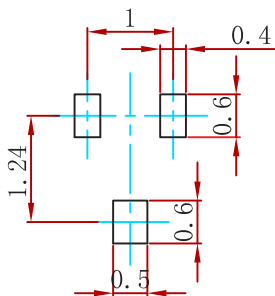
Symbol	Characteristic	Min	Typ	Max	Unit	
R1	Input Resistor	DTC114EE--MS	7.0	10	13	KΩ
		DTC124EE-MS	15.4	22	28.6	
		DTC144EE-MS	32.9	47	61.1	
		DTC114YE-MS	7.0	10	13	
		DTC114TE-MS	7.0	10	13	
		DTC143TE-MS	3.3	4.7	6.1	
		DTC123EE-MS	1.5	2.2	2.9	
		DTC143EE-MS	3.3	4.7	6.1	
		DTC143ZE-MS	3.3	4.7	6.1	
		DTC124XE-MS	15.4	22	28.6	
		DTC123JE-MS	1.54	2.2	2.86	
R1/R2	Resistor Ratio	DTC114EE-MS	0.8	1.0	1.2	--
		DTC124EE-MS	0.8	1.0	1.2	
		DTC144EE-MS	0.8	1.0	1.2	
		DTC114YE-MS	0.17	0.21	0.25	
		DTC114TE-MS	-	-	-	
		DTC143TE-MS	-	-	-	
		DTC123EE-MS	0.8	1.0	1.2	
		DTC143EE-MS	0.8	1.0	1.2	
		DTC143ZE-MS	0.055	0.1	0.185	
		DTC124XE-MS	0.38	0.47	0.56	
		DTC123JE-MS	0.038	0.047	0.056	

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
DTCXXXXX-MS	SOT-523	3000

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